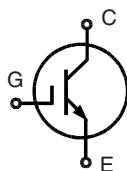
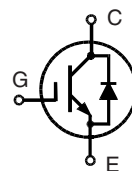


High Voltage IGBT with optional Diode

Short Circuit SOA Capability
Square RBSOA



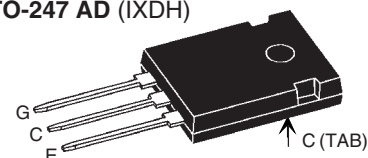
IXDH 30N120



IXDH 30N120 D1

$$\begin{aligned} V_{CES} &= 1200 \text{ V} \\ I_{C25} &= 60 \text{ A} \\ V_{CE(sat) \text{ typ}} &= 2.4 \text{ V} \end{aligned}$$

TO-247 AD (IXDH)



G = Gate,
C = Collector ,

E = Emitter
TAB = Collector

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C}$ to 150°C	1200	V
V_{CGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GE} = 20 \text{ k}\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	60	A
I_{C90}	$T_C = 90^\circ\text{C}$	38	A
I_{CM}	$T_C = 90^\circ\text{C}$; $t_p = 1 \text{ ms}$	76	A
RBSOA	$V_{GE} = \pm 15 \text{ V}$; $T_J = 125^\circ\text{C}$; $R_G = 47 \Omega$ Clamped inductive load; $L = 30 \mu\text{H}$	$I_{CM} = 50$ $V_{CEK} < V_{CES}$	A
t_{SC} (SCSOA)	$V_{GE} = \pm 15 \text{ V}$; $V_{CE} = V_{CES}$; $T_J = 125^\circ\text{C}$ $R_G = 47 \Omega$, non repetitive	10	μs
P_C	$T_C = 25^\circ\text{C}$; IGBT Diode	300 135	W W
T_J		-55 ... +150	$^\circ\text{C}$
T_{stg}		-40 ... +150	$^\circ\text{C}$
M_d	Mounting torque	1.1/10	Nm/lb.in.
Weight		6	g

Features

- NPT IGBT technology
- low saturation voltage
- low switching losses
- square RBSOA, no latch up
- high short circuit capability
- positive temperature coefficient for easy paralleling
- MOS input, voltage controlled
- optional ultra fast diode
- International standard packages

Advantages

- Space savings
- High power density
- IXDT:
surface mountable high power package

Typical Applications

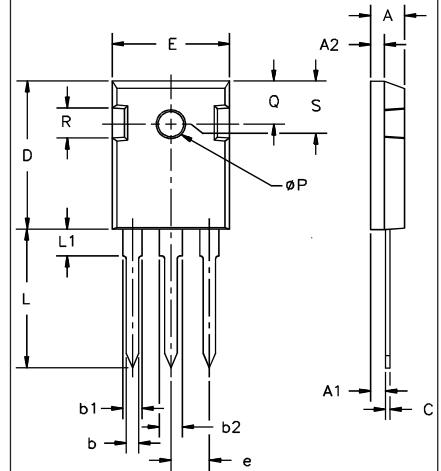
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$	1200		V
$V_{GE(th)}$	$I_C = 1 \text{ mA}$; $V_{CE} = V_{GE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}$; $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$		2.5	1.5 mA mA
I_{GES}	$V_{CE} = 0 \text{ V}$; $V_{GE} = \pm 20 \text{ V}$			$\pm 500 \text{ nA}$
$V_{CE(sat)}$	$I_C = 30 \text{ A}$; $V_{GE} = 15 \text{ V}$		2.4	2.9 V

Symbol	Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
C_{ies} C_{oes} C_{res}	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		1650 250 110	pF pF pF
Q_g	$I_C = 30\text{ A}; V_{GE} = 15\text{ V}; V_{CE} = 0.5 V_{CES}$		120	nC
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 30\text{ A}; V_{GE} = \pm 15\text{ V};$ $V_{CE} = 600\text{ V}; R_G = 47\ \Omega$		100 70 500 70 4.6 3.4	ns ns ns ns mJ mJ
R_{thJC} R_{thCK}	Package with heatsink compound		0.25	0.42 K/W K/W

Reverse Diode (FRED) [D1 version only]		Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
Symbol	Conditions	min.	typ.	max.
V_F	$I_F = 30\text{ A}; V_{GE} = 0\text{ V}$ $I_F = 30\text{ A}; V_{GE} = 0\text{ V}; T_J = 125^\circ\text{C}$	2.5 2.0		2.7 V V
I_F	$T_C = 25^\circ\text{C}$ $T_C = 90^\circ\text{C}$			60 A 35 A
I_{RM} t_{rr}	$I_F = 30\text{ A}; -di_F/dt = 400\text{ A}/\mu\text{s}; V_R = 600\text{ V}$ $V_{GE} = 0\text{ V}; T_J = 125^\circ\text{C}$	20 200		A ns
t_{rr}	$I_F = 1\text{ A}; -di_F/dt = 100\text{ A}/\mu\text{s}; V_R = 30\text{ V}; V_{GE} = 0\text{ V}$	40		ns
R_{thJC}				1 K/W

TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

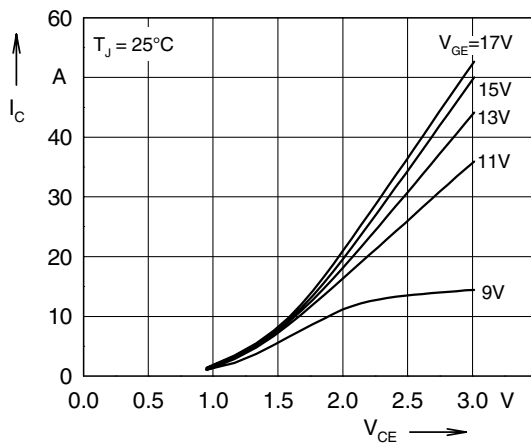


Fig. 1 Typ. output characteristics

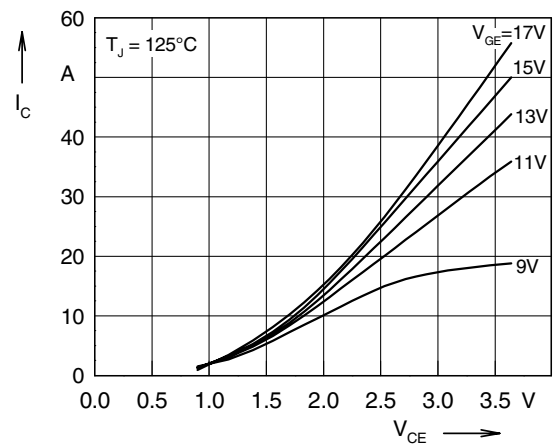


Fig. 2 Typ. output characteristics

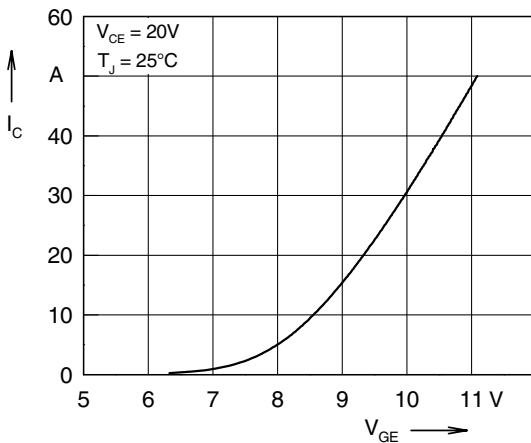


Fig. 3 Typ. transfer characteristics

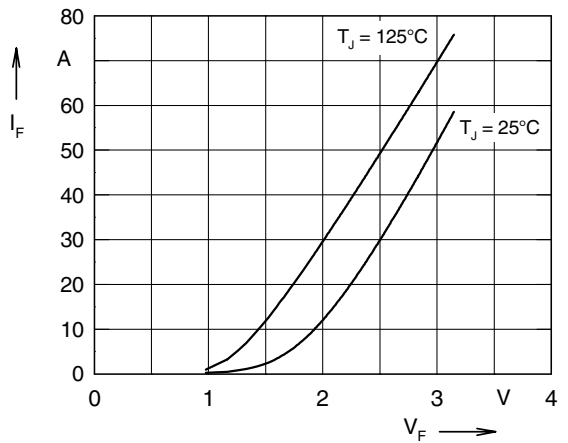


Fig. 4 Typ. forward characteristics of free wheeling diode

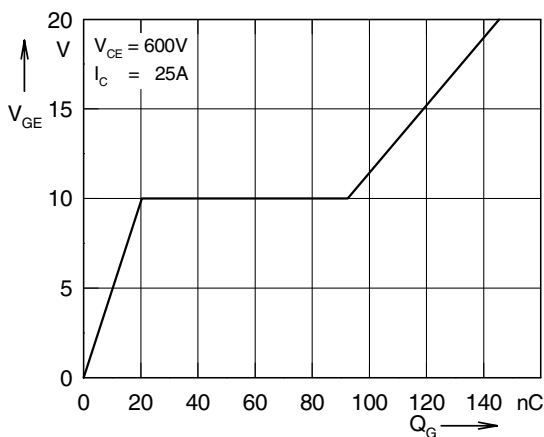


Fig. 5 Typ. turn on gate charge

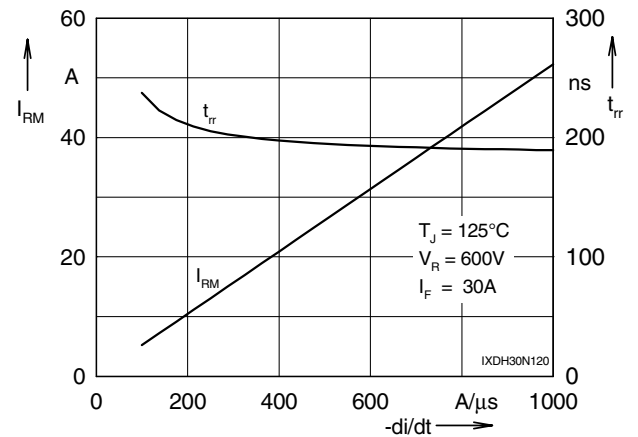


Fig. 6 Typ. turn off characteristics of free wheeling diode

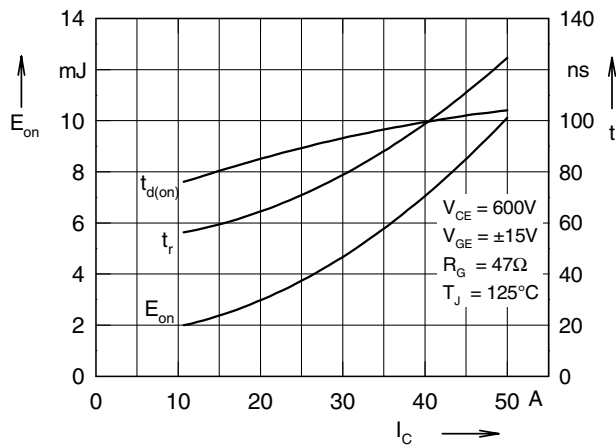


Fig. 7 Typ. turn on energy and switching times versus collector current

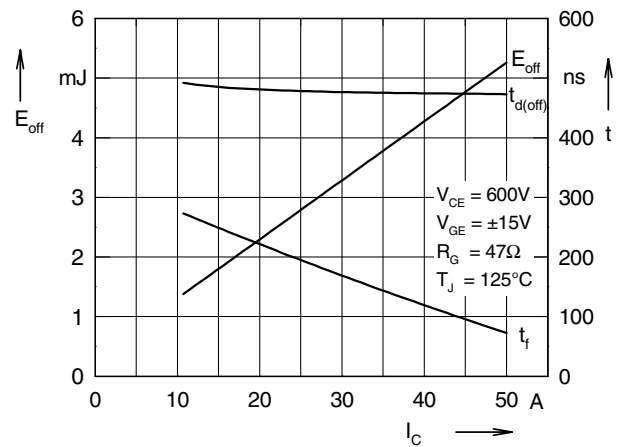


Fig. 8 Typ. turn off energy and switching times versus collector current

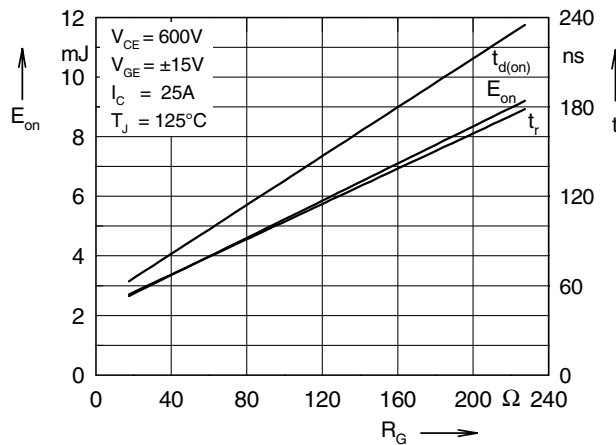


Fig. 9 Typ. turn on energy and switching times versus gate resistor

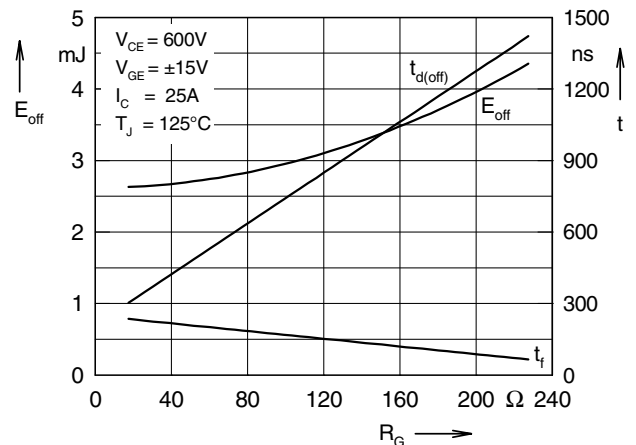


Fig. 10 Typ. turn off energy and switching times versus gate resistor

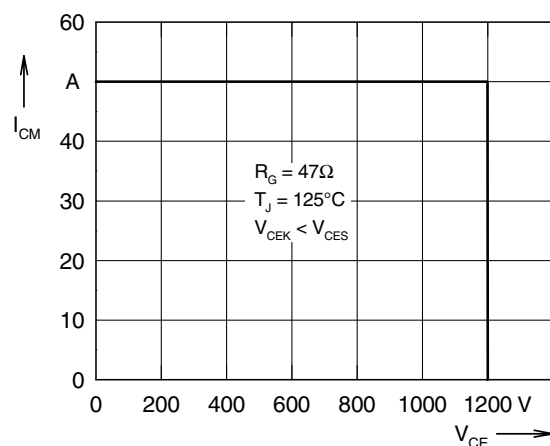


Fig. 11 Reverse biased safe operating area RBSOA

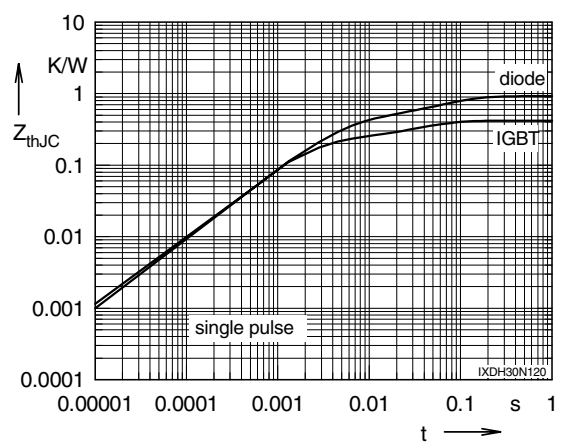


Fig. 12 Typ. transient thermal impedance



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